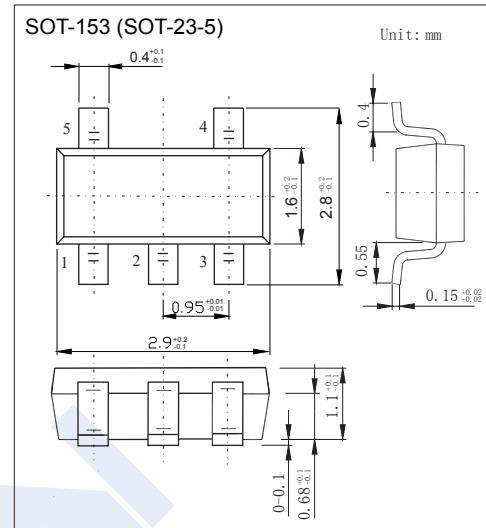
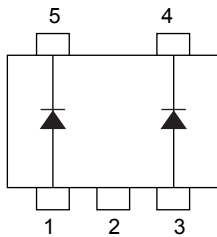


Schottky Diodes

SBE807 (KBE807)

■ Features

- Low switching noise.
- Low reverse current
- High frequency rectification

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Repetitive Peak Reverse Voltage	VRRM	30	V
Nonrepetitive Peak Reverse Surge Voltage	VRSM	35	
Average Output Current	I_o	1	A
Surge Forward Current @ 50Hz	IFSM	10	
Thermal Resistance Junction to Ambient	R θ JA	111	$^\circ\text{C}/\text{W}$
Junction Temperature	TJ	125	$^\circ\text{C}$
Storage Temperature range	Tstg	-55 to 125	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	VR	IR= 0.2mA	30			V
Forward voltage	VF	IF= 0.7 A			0.5	
		IF= 1 A			0.53	
Reverse voltage leakage current	IR	VR= 16 V			15	μA
Junction capacitance	Cj	VR= 10 V, f= 1 MHz		27		pF
Reverse recovery time	trr	IF=IR=100mA, Irr=0.1xIR, RL=100 Ω			10	ns

■ Marking

Marking	SJ

Schottky Diodes

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Typical Characteristics

